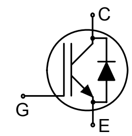
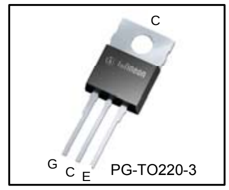
Low Loss DuoPack : IGBT in TRENCHSTOP™ and Fieldstop technology with soft, fast recovery anti-parallel Emitter Controlled HE diode





- Very low $V_{CE(sat)}$ 1.5V (typ.)
- Maximum Junction Temperature 175°C
- Short circuit withstand time 5 µs
- Designed for :
  - Frequency Converters
  - Drives
- TRENCHSTOP™ and Fieldstop technology for 600V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
  - very high switching speed
  - low $V_{CE(sat)}$
- Positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Very soft, fast recovery anti-parallel Emitter Controlled HE diode
- Qualified according to JEDEC[1] for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : http://www.infineon.com/igbt/

Type	V_{CE}	I_C	$V_{CE(sat),Tj=25°C}$	$T_{j,max}$	Marking	Package
IKP04N60T	600 V	4 A	1.5 V	175 °C	K04T60	PG-TO220-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage , $T_j \geq 25°C$	V_{CE}	600	V
DC collector current, limited by T_{jmax} $T_C = 25°C$ $T_C = 100°C$	I_C	 8 4	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	12	
Turn off safe operating area, $V_{CE} = 600V$, $T_j = 175°C$, $t_p = 1µs$	-	12	
Diode forward current, limited by T_{jmax} $T_C = 25°C$ $T_C = 100°C$	I_F	 8 4	
Diode pulsed current, t_p limited by T_{jmax}	I_{Fpuls}	12	
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time[2)] $V_{GE} = 15V$, $V_{CC} \leq 400V$, $T_j \leq 150°C$	t_{SC}	5	µs
Power dissipation $T_C = 25°C$	P_{tot}	42	W
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

[1] J-STD-020 and JESD-022

[2)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		3.5	K/W
Diode thermal resistance, junction – case	R_{thJCD}		5	
Thermal resistance, junction – ambient	R_{thJA}		62	

Electrical Characteristic, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V, I_C=0.2mA	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C=4A T_j=25°C T_j=175°C	 - -	 1.5 1.9	 2.05 -	
Diode forward voltage	V_F	V_{GE}=0V, I_F=4A T_j=25°C T_j=175°C	 - -	 1.65 1.6	 2.05 -	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C= 60µA, V_{CE}=V_{GE}	4.1	4.9	5.7	
Zero gate voltage collector current	I_{CES}	V_{CE}=600V, V_{GE}=0V T_j=25°C T_j=175°C	 - -	 - -	 40 1000	µA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE}=20V, I_C=4A	-	2.2	-	S
Integrated gate resistor	R_{Gint}			-		Ω

Dynamic Characteristic

Parameter	Symbol	Conditions	min.	Typ.	max.	Unit
Input capacitance	C_{ies}	V_{CE}=25V,	-	252	-	pF
Output capacitance	C_{oes}	V_{GE}=0V,	-	20	-	
Reverse transfer capacitance	C_{res}	f=1MHz	-	7.5	-	
Gate charge	Q_{Gate}	V_{CC}=480V, I_C=4A V_{GE}=15V	-	27	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7	-	nH
Short circuit collector current[1)]	$I_{C(SC)}$	V_{GE}=15V, t_{SC}≤5µs V_{CC} = 400V, T_j ≤ 150°C	-	36	-	A

1) Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at T_j=25 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=25°C, V_{CC}=400V, I_C=4A, V_{GE}=0/15V, R_G= 47 Ω, L_σ [1)]=150nH, C_σ [1)]=47pF Energy losses include "tail" and diode reverse recovery.	-	14	-	ns
Rise time	t_r		-	7	-	
Turn-off delay time	$t_{d(off)}$		-	164	-	
Fall time	t_f		-	43	-	
Turn-on energy	E_{on}		-	61	-	µJ
Turn-off energy	E_{off}		-	84	-	
Total switching energy	E_{ts}		-	145	-	
Anti-Parallel Diode Characteristic						
Diode reverse recovery time	t_{rr}	T_j=25°C,	-	28	-	ns
Diode reverse recovery charge	Q_{rr}	V_R=400V, I_F=4A,	-	79	-	nC
Diode peak reverse recovery current	I_{rrm}	di_F/dt=610A/µs	-	5.3	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	346	-	A/µs

Switching Characteristic, Inductive Load, at T_j=175 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=175°C, V_{CC}=400V, I_C=4A, V_{GE}=0/15V, R_G= 47 Ω L_σ [1)]=150nH, C_σ [1)]=47pF Energy losses include "tail" and diode reverse recovery.	-	14	-	ns
Rise time	t_r		-	10	-	
Turn-off delay time	$t_{d(off)}$		-	185	-	
Fall time	t_f		-	83	-	
Turn-on energy	E_{on}		-	99	-	µJ
Turn-off energy	E_{off}		-	97	-	
Total switching energy	E_{ts}		-	196	-	
Anti-Parallel Diode Characteristic						
Diode reverse recovery time	t_{rr}	T_j=175°C	-	95	-	ns
Diode reverse recovery charge	Q_{rr}	V_R=400V, I_F=4A,	-	291	-	nC
Diode peak reverse recovery current	I_{rrm}	di_F/dt=610A/µs	-	6.6	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	253	-	A/µs

[1)] Leakage inductance L_σ and Stray capacity C_σ due to dynamic test circuit in Figure E.

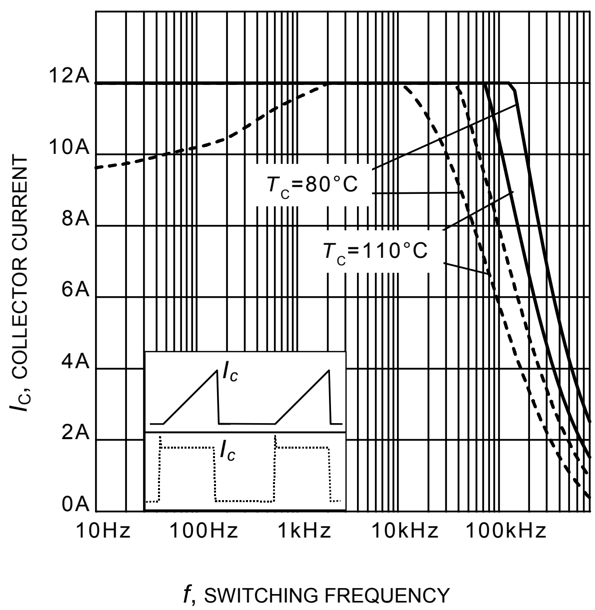


Figure 1. Collector current as a function of switching frequency
($T_j \leq 175°C$, $D = 0.5$, $V_{CE} = 400V$, $V_{GE} = 0/15V$, $R_G = 47\Omega$)

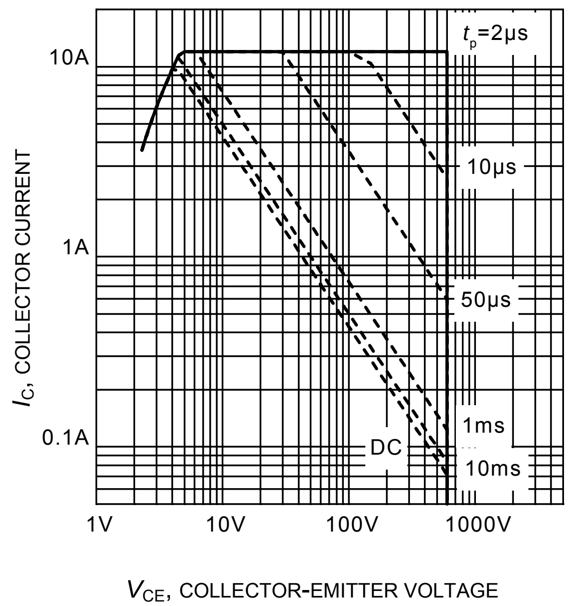


Figure 2. Safe operating area
($D = 0$, $T_C = 25°C$, $T_j \leq 175°C$; V_{GE}=0/15V)

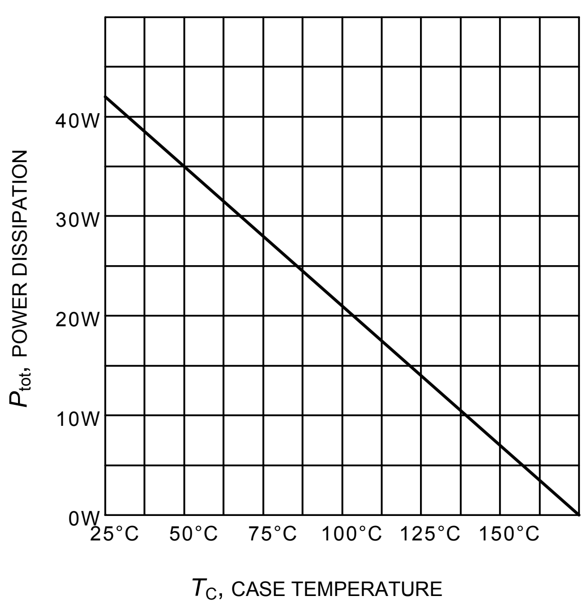


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 175°C$)

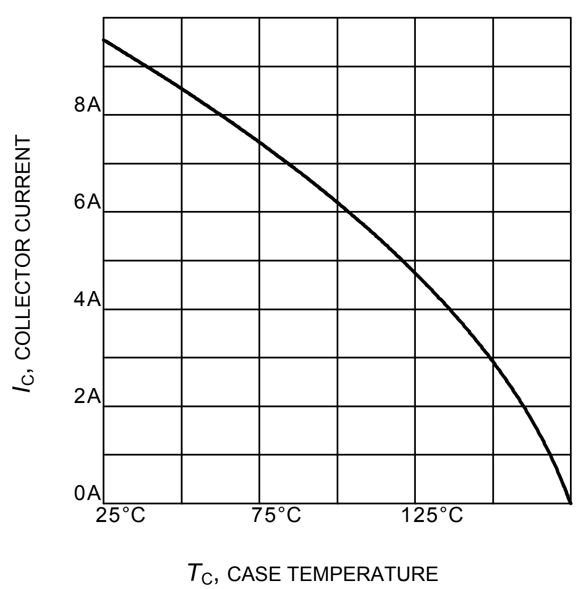


Figure 4. Collector current as a function of case temperature
($V_{GE} \geq 15V$, $T_j \leq 175°C$)

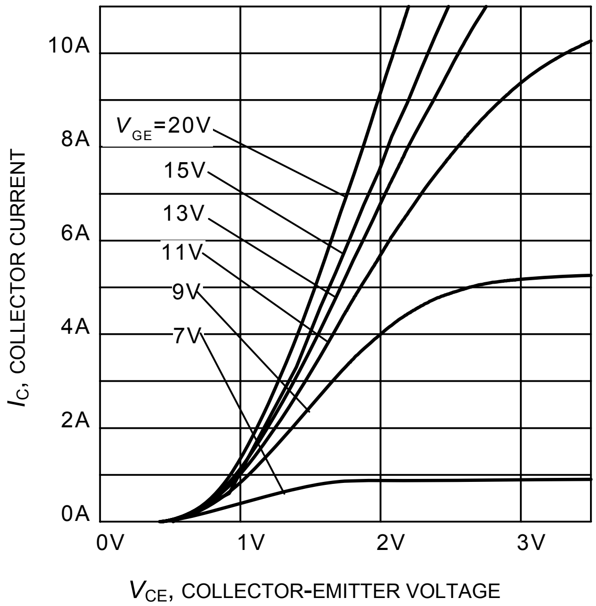


Figure 5. Typical output characteristic
(T_j = 25°C)

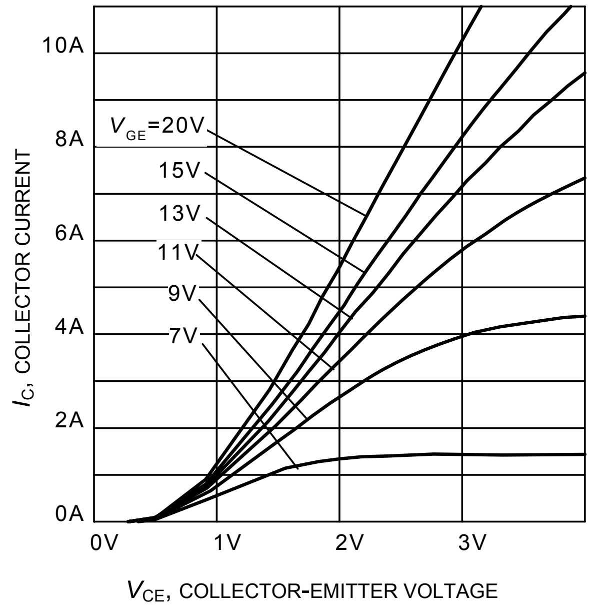


Figure 6. Typical output characteristic
(T_j = 175°C)

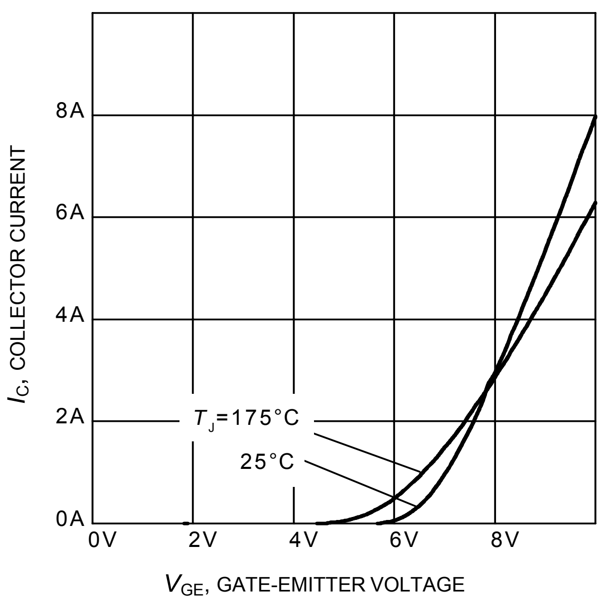


Figure 7. Typical transfer characteristic
(V_{CE}=20V)

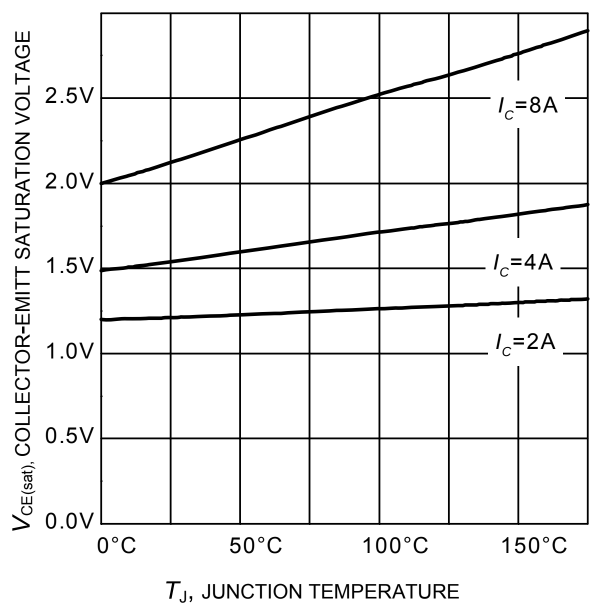


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE} = 15V)

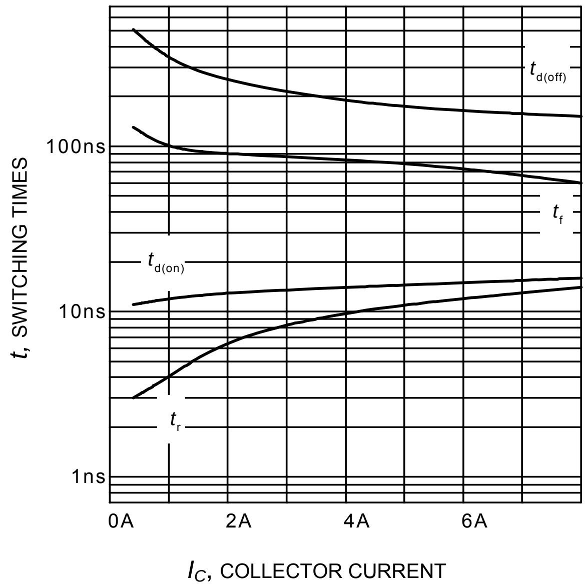


Figure 9. Typical switching times as a function of collector current
(inductive load, T_J=175°C, V_{CE} = 400V, V_{GE} = 0/15V, R_G = 47Ω, Dynamic test circuit in Figure E)

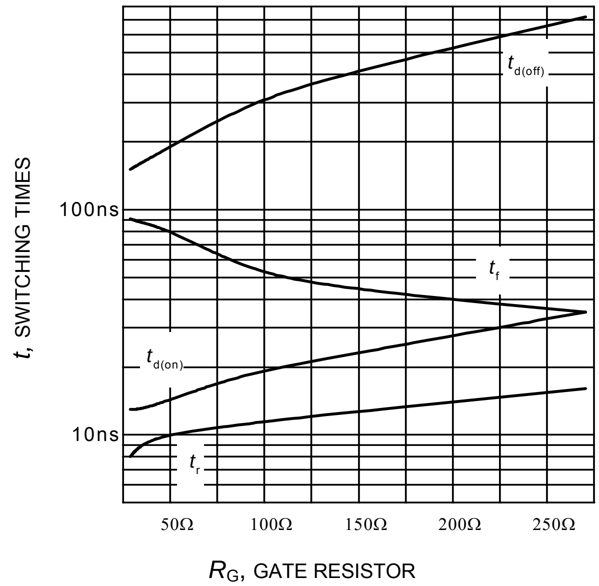


Figure 10. Typical switching times as a function of gate resistor
(inductive load, T_J = 175°C, V_{CE}= 400V, V_{GE} = 0/15V, I_C = 4A, Dynamic test circuit in Figure E)

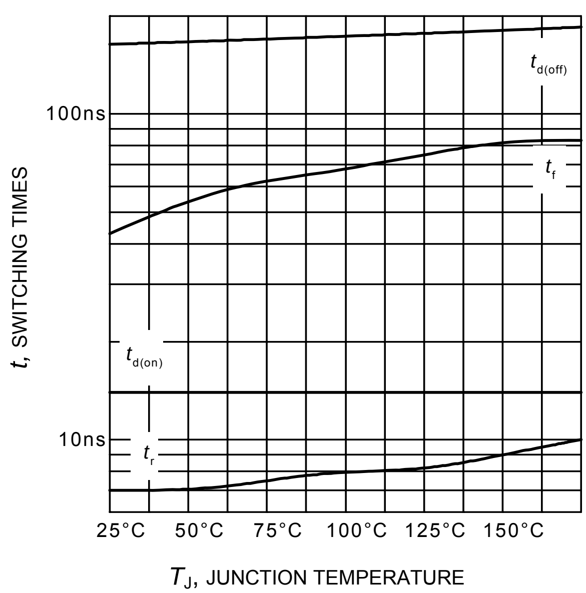


Figure 11. Typical switching times as a function of junction temperature
(inductive load, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 4A, R_G=47Ω, Dynamic test circuit in Figure E)

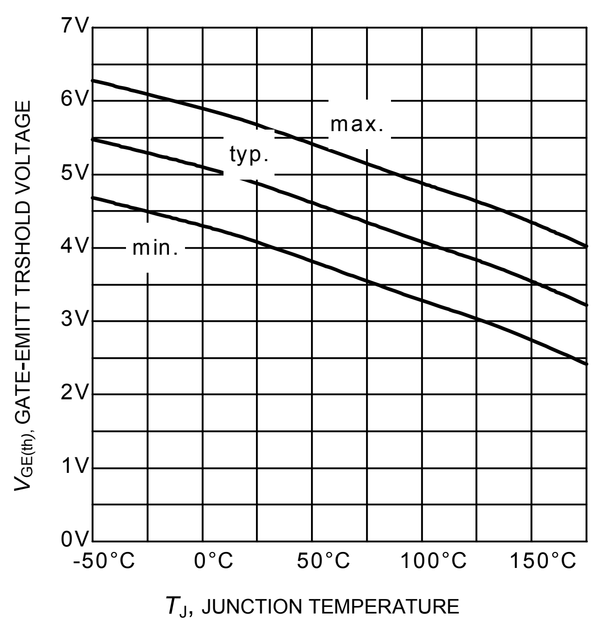


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C = 60 µA)

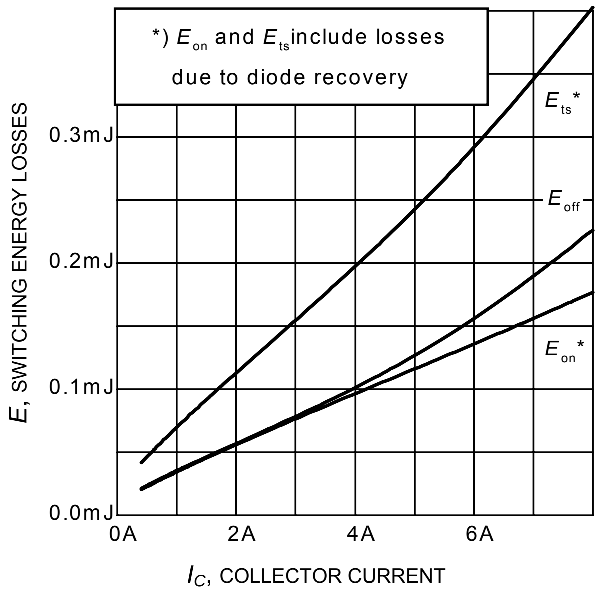


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, T_J = 175°C, V_{CE} = 400V, V_{GE} = 0/15V, R_G = 47Ω, Dynamic test circuit in Figure E)

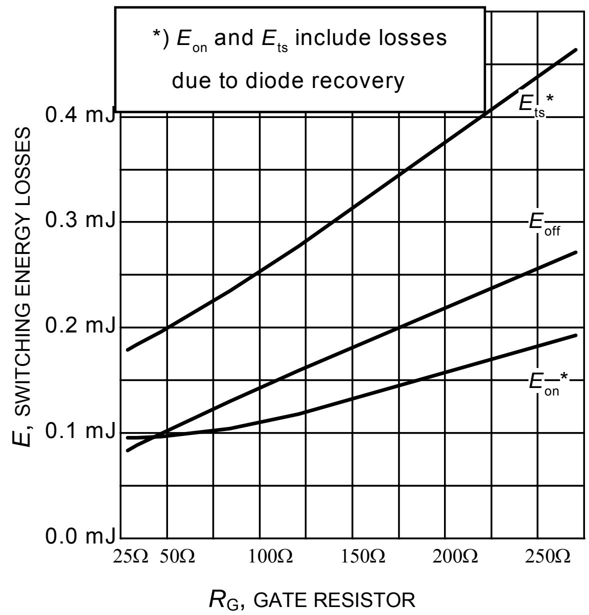


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, T_J = 175°C, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 4A, Dynamic test circuit in Figure E)

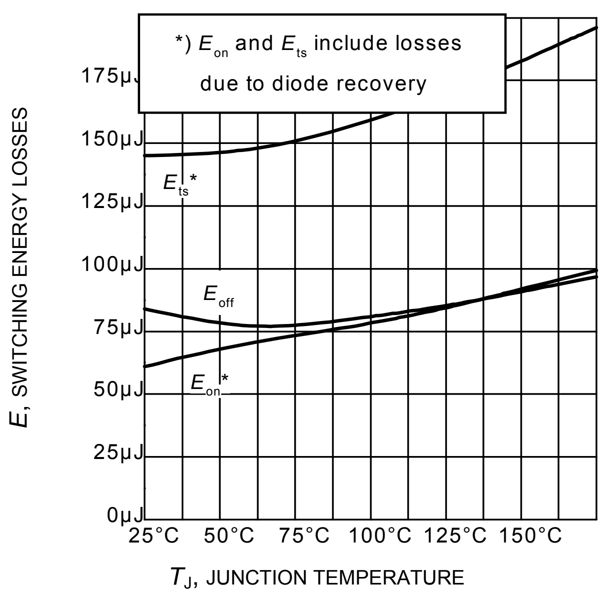


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 4A, R_G = 47Ω, Dynamic test circuit in Figure E)

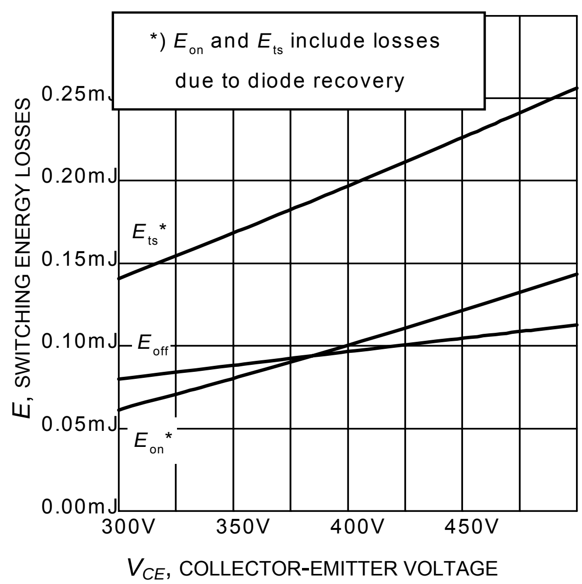


Figure 16. Typical switching energy losses as a function of collector emitter voltage
(inductive load, T_J = 175°C, V_{GE} = 0/15V, I_C = 4A, R_G = 47Ω, Dynamic test circuit in Figure E)

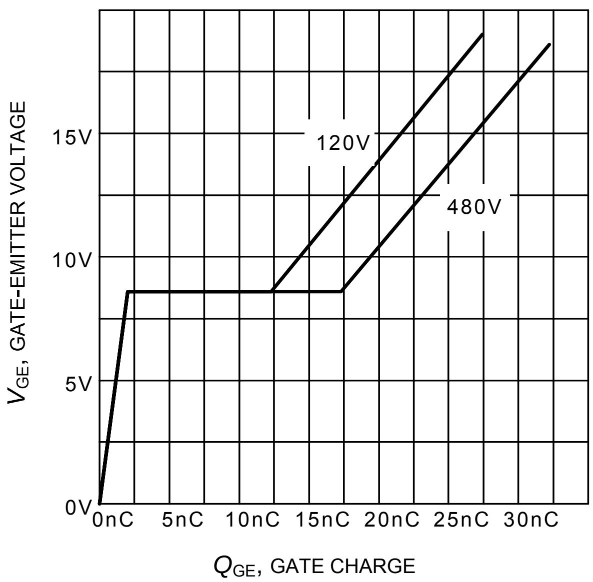


Figure 17. Typical gate charge
(I_C=4 A)

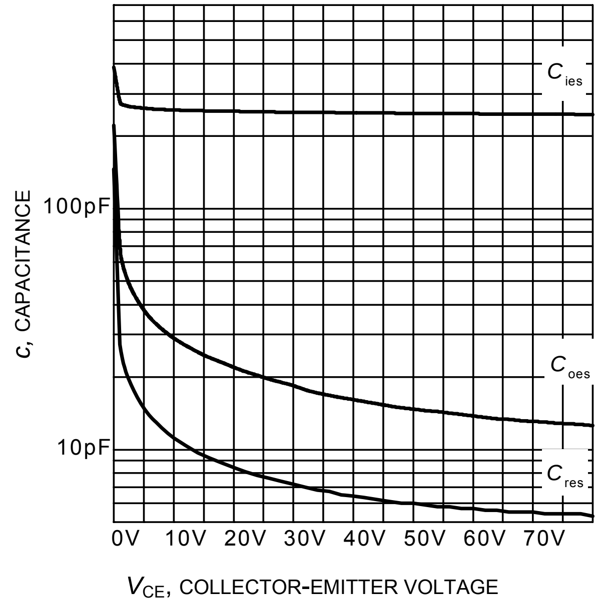


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE}=0V, f = 1 MHz)

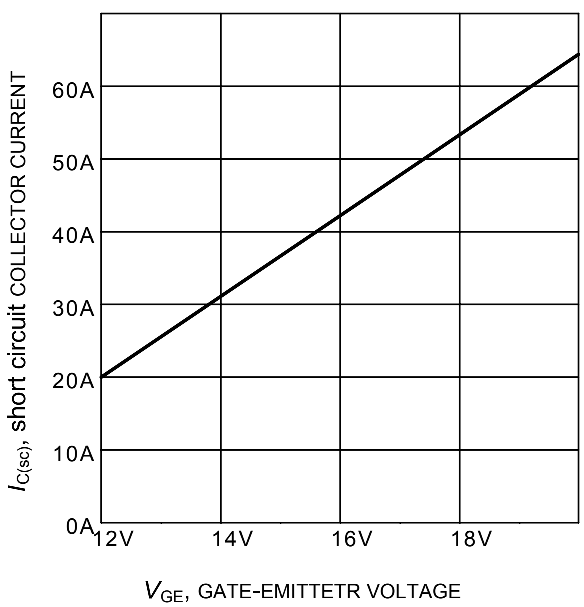


Figure 19. Typical short circuit collector current as a function of gate-emitter voltage
(V_{CE} ≤ 400V, T_j ≤ 150°C)

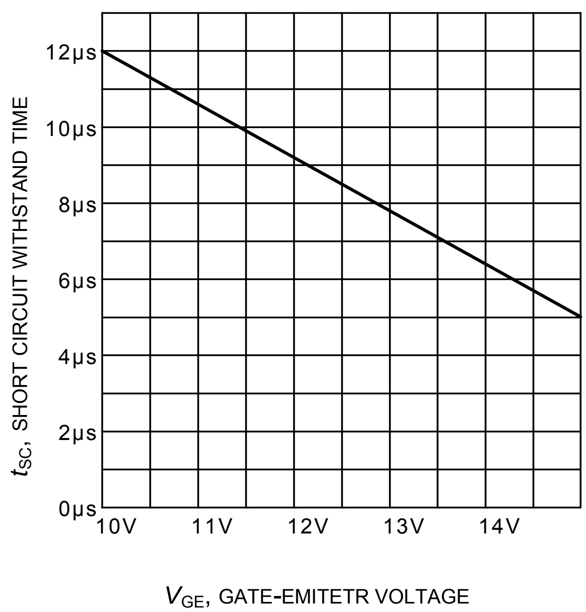


Figure 20. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE}=400V, start at T_J=25°C, T_{Jmax}<150°C)

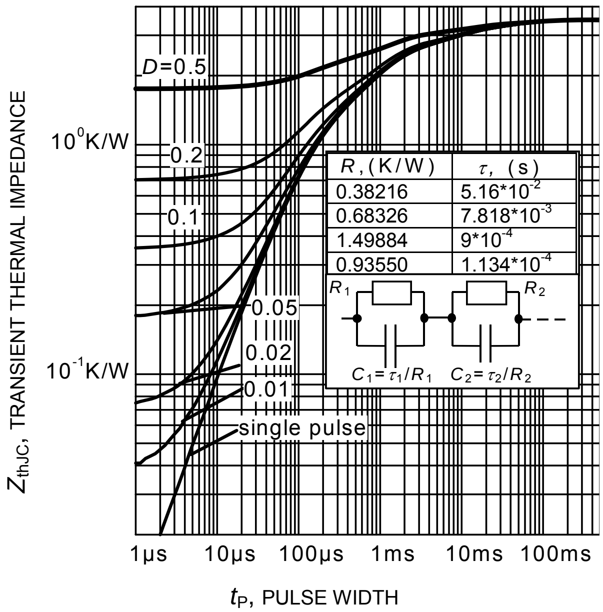


Figure 21. IGBT transient thermal impedance
($D = t_p / T$)

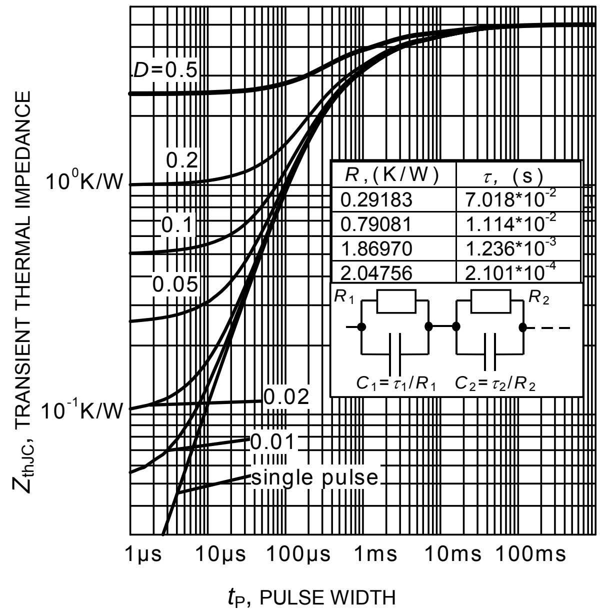


Figure 22. Diode transient thermal impedance as a function of pulse width
($D=t_P/T$)

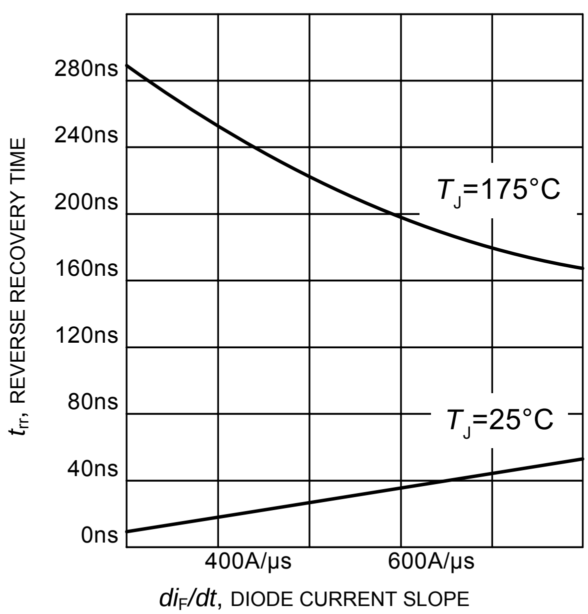


Figure 23. Typical reverse recovery time as a function of diode current slope
(V_R=400V, I_F=4A,
Dynamic test circuit in Figure E)

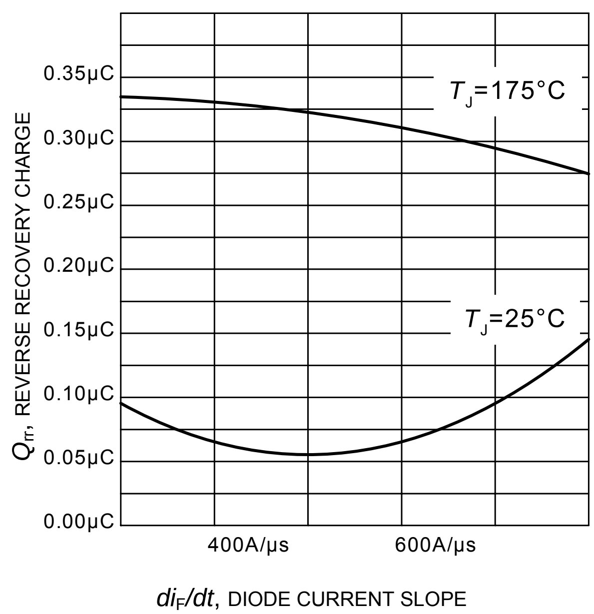


Figure 24. Typical reverse recovery charge as a function of diode current slope
(V_R = 400V, I_F = 4A,
Dynamic test circuit in Figure E)

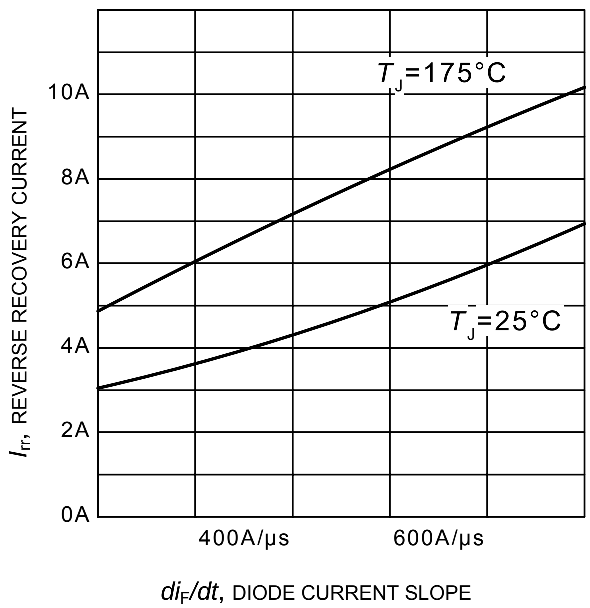


Figure 25. Typical reverse recovery current as a function of diode current slope
(V_R = 400V, I_F = 4A,
Dynamic test circuit in Figure E)

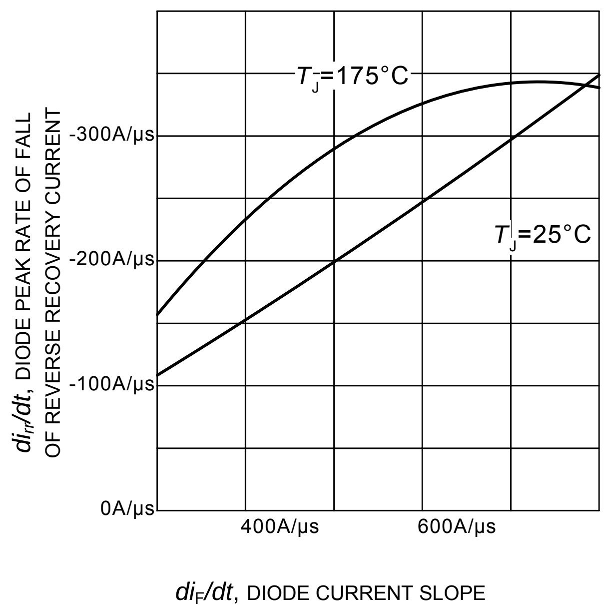


Figure 26. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
(V_R=400V, I_F=4A,
Dynamic test circuit in Figure E)

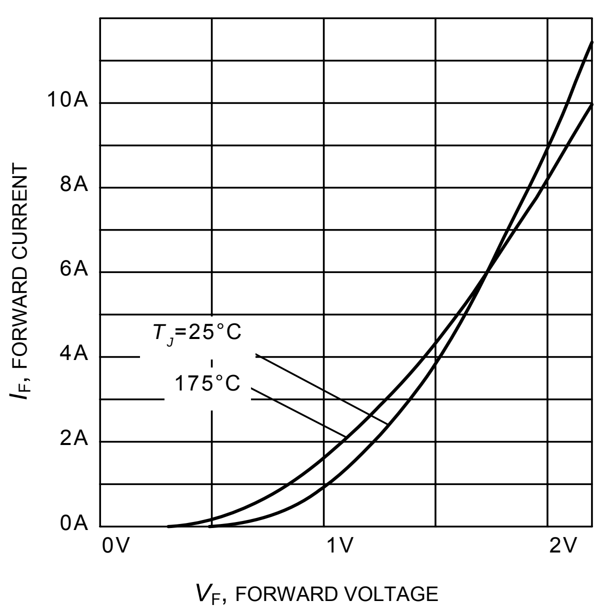


Figure 27. Typical diode forward current as a function of forward voltage

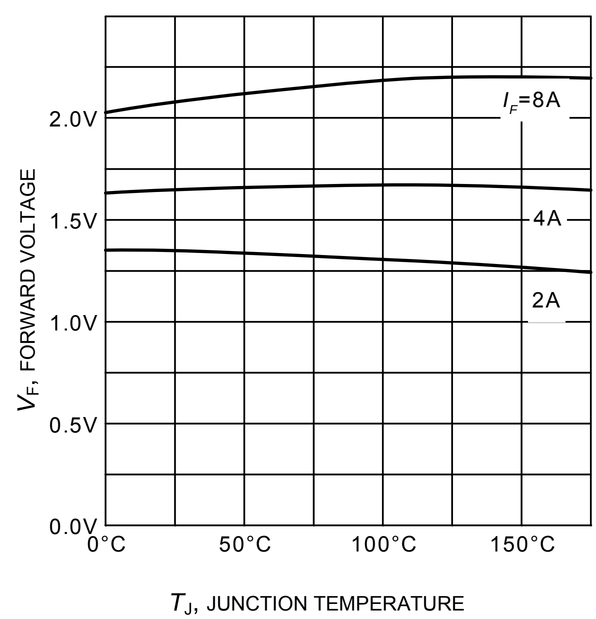
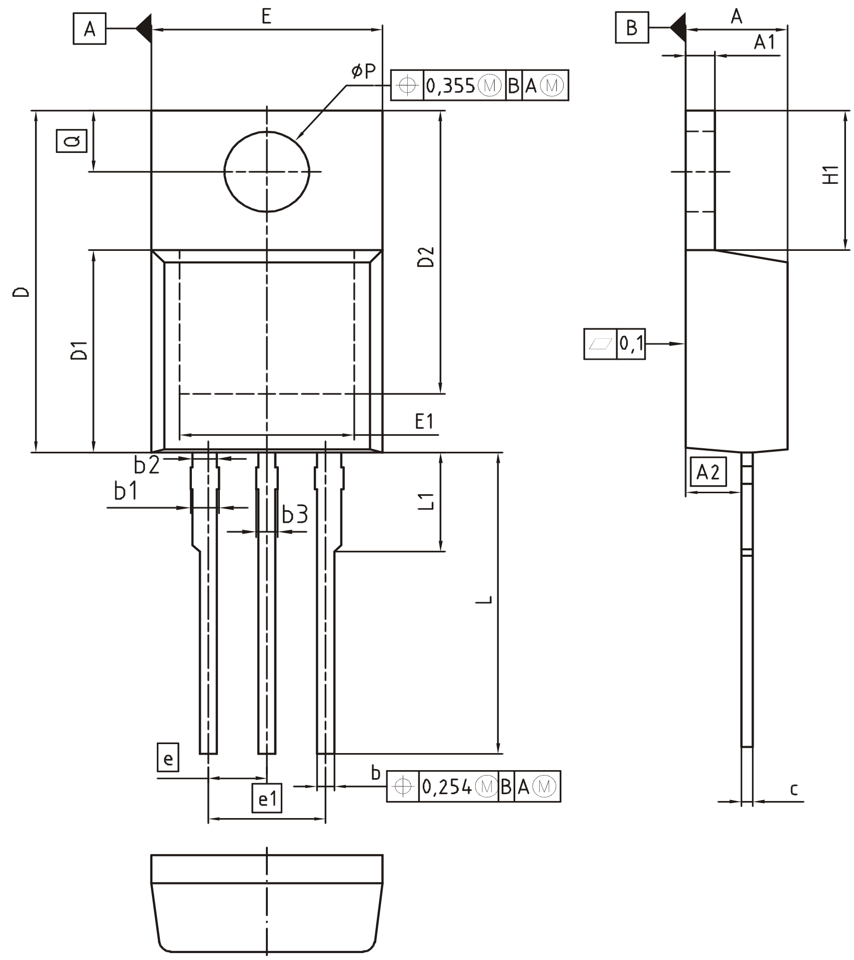


Figure 28. Typical diode forward voltage as a function of junction temperature

PG-TO220-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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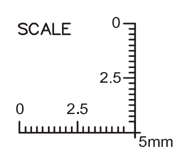

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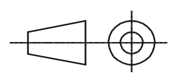

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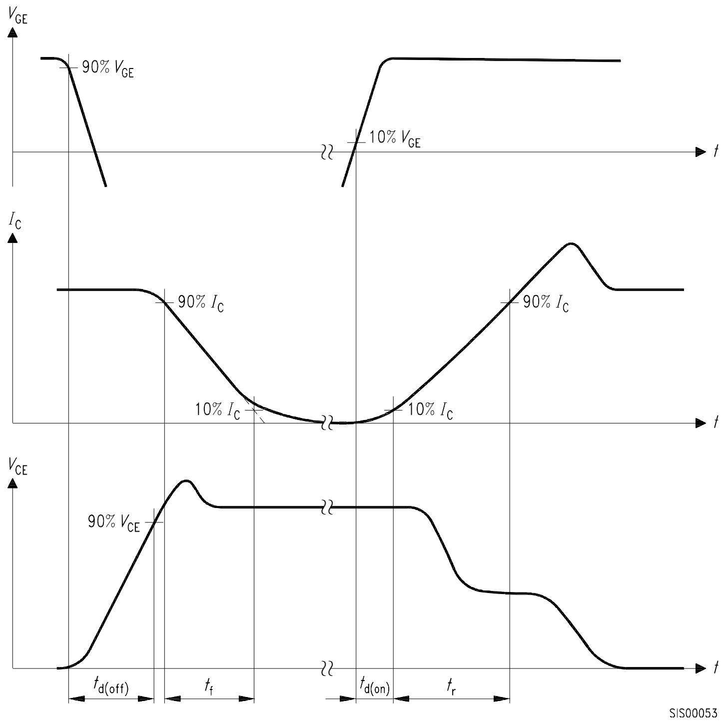

Figure A. Definition of switching times

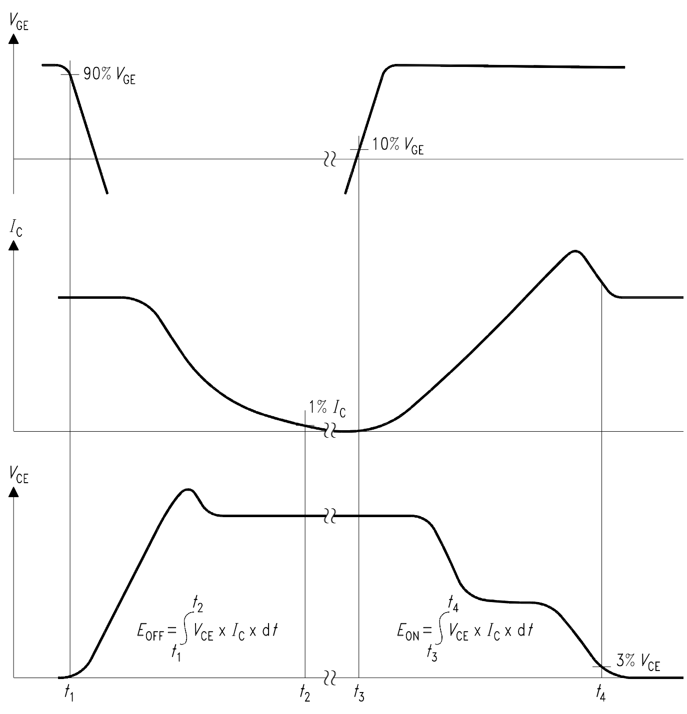

Figure B. Definition of switching losses

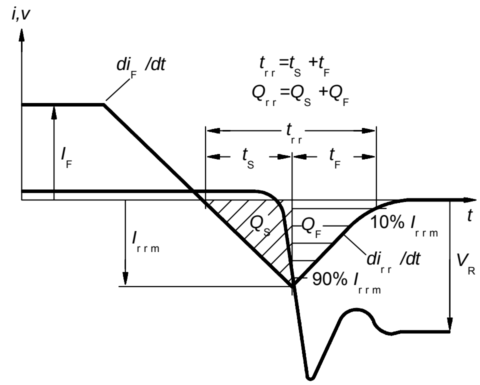

Figure C. Definition of diodes switching characteristics

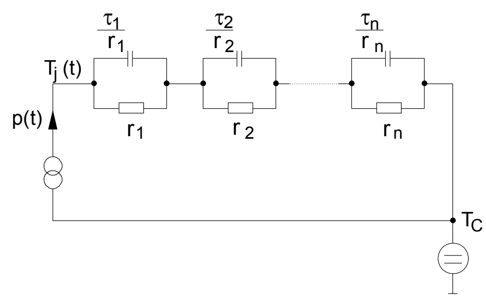

Figure D. Thermal equivalent circuit

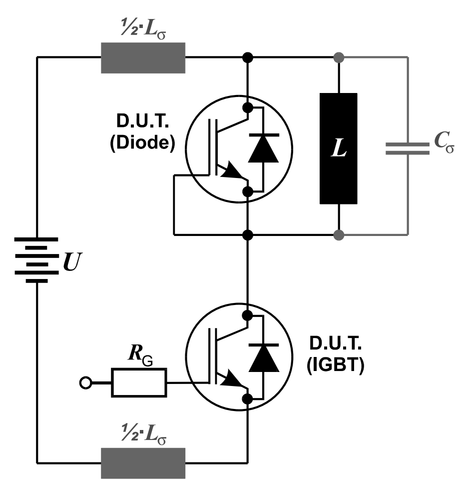

Figure E. Dynamic test circuit

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